Complementary Power Transistors

DPAK for Surface Mount Applications

Designed for general purpose amplifier and low speed switching applications.

Features

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("-1" Suffix)
- Electrically Similar to MJE2955 and MJE3055
- High Current Gain-Bandwidth Product
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V _{CEO}	60	Vdc
Collector-Base Voltage	V _{CB}	70	Vdc
Emitter-Base Voltage	V _{EB}	5	Vdc
Collector Current	I _C	10	Adc
Base Current	I _B	6	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D [†]	20 0.16	W W/°C
Total Power Dissipation (Note 1) @ T _A = 25°C Derate above 25°C	P _D	1.75 0.014	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C
ESD - Human Body Model	HBM	3B	V
ESD – Machine Model	MM	С	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

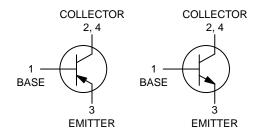


ON Semiconductor®

http://onsemi.com

SILICON POWER TRANSISTORS 10 AMPERES 60 VOLTS, 20 WATTS

COMPLEMENTARY





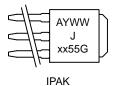


DPAK CASE 369C STYLE 1

IPAK CASE 369D STYLE 1

MARKING DIAGRAMS





DPAK

= Assembly Location

Y = Year

WW = Work Week

Jxx55 = Device Code

x = 29 or 30

G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

[†]Safe Area Curves are indicated by Figure 1. Both limits are applicable and must be observed.

These ratings are applicable when surface mounted on the minimum pad sizes recommended.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	6.25	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	71.4	°C/W

^{2.} These ratings are applicable when surface mounted on the minimum pad sizes recommended.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS			•	*
Collector–Emitter Sustaining Voltage (Note 3) $(I_C = 30 \text{ mAdc}, I_B = 0)$	V _{CEO(sus)}	60	_	Vdc
Collector Cutoff Current (V _{CE} = 30 Vdc, I _B = 0)	I _{CEO}	-	50	μAdc
Collector Cutoff Current $(V_{CE} = 70 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc})$ $(V_{CE} = 70 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}, T_{C} = 150^{\circ}\text{C})$	ICEX	- -	0.02 2	mAdc
Collector Cutoff Current $(V_{CB} = 70 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 70 \text{ Vdc}, I_E = 0, T_C = 150^{\circ}\text{C})$	Ісво	- -	0.02 2	mAdc
Emitter Cutoff Current (V _{BE} = 5 Vdc, I _C = 0)	I _{EBO}	-	0.5	mAdc
ON CHARACTERISTICS				
DC Current Gain (Note 3) ($I_C = 4$ Adc, $V_{CE} = 4$ Vdc) ($I_C = 10$ Adc, $V_{CE} = 4$ Vdc)	h _{FE}	20 5	100	-
Collector–Emitter Saturation Voltage (Note 3) $(I_C = 4 \text{ Adc}, I_B = 0.4 \text{ Adc})$ $(I_C = 10 \text{ Adc}, I_B = 3.3 \text{ Adc})$	V _{CE(sat)}	- -	1.1 8	Vdc
Base–Emitter On Voltage (Note 3) (I _C = 4 Adc, V _{CE} = 4 Vdc)	V _{BE(on)}	-	1.8	Vdc
DYNAMIC CHARACTERISTICS			•	•
Current–Gain – Bandwidth Product (I _C = 500 mAdc, V _{CE} = 10 Vdc, f = 500 kHz)	f _T	2	_	MHz
Pulsa Tast: Pulsa Width < 300 us Duty Cycla < 2%			•	*

^{3.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.

TYPICAL CHARACTERISTICS

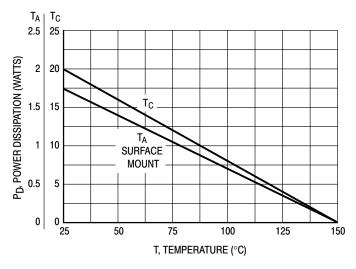


Figure 1. Power Derating

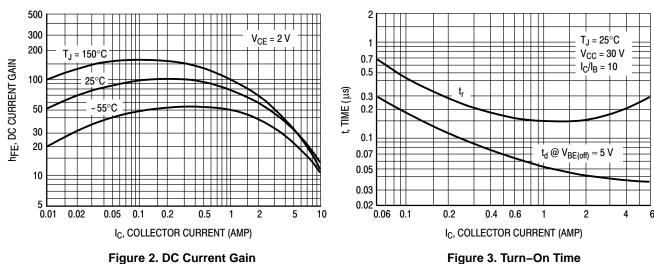


Figure 2. DC Current Gain

1.4 $T_J = 25^{\circ}C$ 3 V_{CC} = 30 V 1.2 $T_J = 25^{\circ}C$ 2 $I_C/I_B = 10$ $I_{B1} = I_{B2}$ V, VOLTAGE (VOLTS) t, TIME (µs) 8.0 $V_{BE(sat)} @ I_C/I_B = 10$ 0.7 0.5 0.6 V_{BE} @ V_{CE} = 2 V0.3 0.2 $t_{\rm f}$ 0.4 0.1 0.2 $V_{CE(sat)} @ I_C/I_B = 10$ 0.07 0 l 10 0.06 0.1 0.6 0.1 0.2 0.3 I_C, COLLECTOR CURRENT (AMP) I_C, COLLECTOR CURRENT (AMP)

Figure 4. "On" Voltages, MJD3055

Figure 5. Turn-Off Time

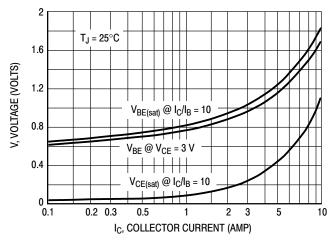
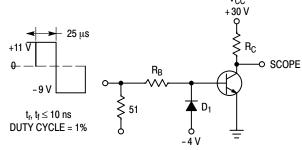


Figure 6. "On" Voltages, MJD2955



 R_B and R_C VARIED TO OBTAIN DESIRED CURRENT LEVELS $D_1 \ \text{MUST BE FAST RECOVERY TYPE, eg:} \\ 1N5825 \ \text{USED ABOVE I}_B \approx 100 \ \text{mA} \\ \text{MSD6100 USED BELOW I}_B \approx 100 \ \text{mA}$

Figure 7. Switching Time Test Circuit

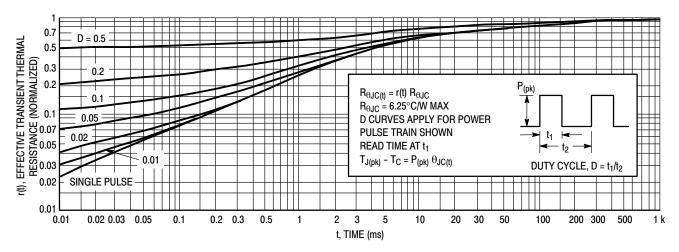


Figure 8. Thermal Response

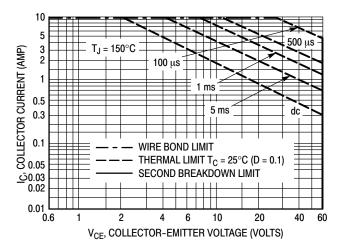


Figure 9. Maximum Forward Bias Safe Operating Area

Forward Bias Safe Operating Area Information

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 9 is based on $T_{J(pk)} = 150^{\circ} C$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ} C$. $T_{J(pk)}$ may be calculated from the data in Figure 8. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

ORDERING INFORMATION

Device	Package Type	Package	Shipping [†]
MJD2955G	DPAK (Pb-Free)	369C	75 Units / Rail
MJD2955-1G	IPAK (Pb-Free)	369D	75 Units / Rail
MJD2955T4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD2955T4G*	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
MJD3055G	DPAK (Pb-Free)	369C	75 Units / Rail
MJD3055T4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD3055T4G*	DPAK (Pb-Free)	369C	2,500 / Tape & Reel

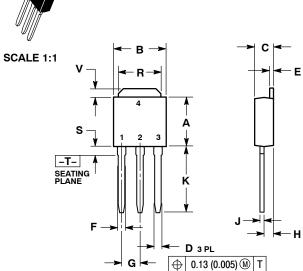
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable

MECHANICAL CASE OUTLINE





DATE 15 DEC 2010



STYLE 2:

PIN 1. GATE

3

STYLE 6: PIN 1. MT1 2. MT2 3. GATE

2. DRAIN

4. DRAIN

MT2

SOURCE

STYLE 1: PIN 1. BASE

3

STYLE 5: PIN 1. GATE

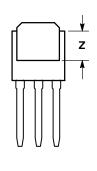
2. ANODE 3. CATHODE

ANODE

2. COLLECTOR

EMITTER

COLLECTOR



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.245	5.97	6.35
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
٧	0.035	0.050	0.89	1.27
Z	0.155		3.93	

MARKING DIAGRAMS

STYLE 3: PIN 1. ANODE

2. CATHODE

4. CATHODE

3 ANODE

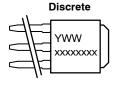
STYLE 7: PIN 1. GATE 2. COLLECTOR

3. EMITTER

COLLECTOR

STYLE 4: PIN 1. CATHODE ANODE
 GATE

4. ANODE



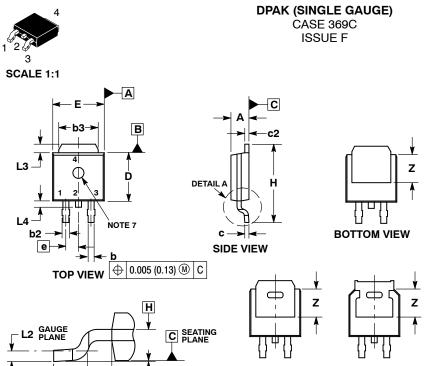


xxxxxxxxx = Device Code Α = Assembly Location IL = Wafer Lot Υ = Year WW = Work Week

DOCUMENT NUMBER:	98AON10528D	Electronic versions are uncontrolled except when accessed directly from the Document Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	IPAK (DPAK INSERTION MOUNT)		PAGE 1 OF 1

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

DATE 21 JUL 2015



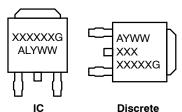
NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: INCHES.
- 3. THERMAL PAD CONTOUR OPTIONAL WITHIN DI-
- MENSIONS b3, L3 and Z.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
 5. DIMENSIONS D AND E ARE DETERMINED AT THE
- OUTERMOST EXTREMES OF THE PLASTIC BODY.

 6. DATUMS A AND B ARE DETERMINED AT DATUM
- 7. OPTIONAL MOLD FEATURE.

	INCHES		MILLIM	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
С	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
е	0.090	BSC	2.29	BSC
Н	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114 REF		2.90 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4		0.040		1.01
Z	0.155		3.93	

GENERIC MARKING DIAGRAM*



XXXXXX = Device Code

= Assembly Location Α

L = Wafer Lot Υ = Year WW = Work Week G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking.

SOLDERING FOOTPRINT*

STYLE 8:

STYLE 3:

PIN 1. N/C 2. CATHODE

3. ANODE 4. CATHODE

PIN 1. ANODE 2. CATHODE

3. ANODE

4. CATHODE

STYLE 9:

PIN 1. ANODE 2. CATHODE

Α1

STYLE 2:

PIN 1. GATE 2. COLLECTOR

3. EMITTER 4. COLLECTOR

PIN 1. GATE 2. DRAIN

SOURCE

4. DRAIN

DETAIL A ROTATED 90° CW

STYLE 7:

STYLE 1:

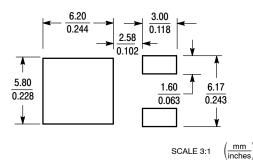
STYLE 6:

PIN 1. MT1 2. MT2

3. GATE 4. MT2

PIN 1. BASE 2. COLLECTOR 3. EMITTER

4. COLLECTOR



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON10527D	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	DPAK (SINGLE GAUGE)		PAGE 1 OF 1

BOTTOM VIEW

ALTERNATE CONSTRUCTIONS

STYLE 5:

STYLE 10:

PIN 1. GATE 2. ANODE 3. CATHODE

4. ANODE

PIN 1. CATHODE 2. ANODE

3. CATHODE 4. ANODE

STYLE 4:

PIN 1. CATHODE 2. ANODE 3. GATE

4. ANODE

3. RESISTOR ADJUST 4. CATHODE

ON Semiconductor and un are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ÓN Semiconductor does not convey any license under its patent rights nor the rights of others

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer pu

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H BC546/116 BC557/116 BSW67A NTE158 NTE187A NTE195A NTE2302 NTE2330 NTE63 C4460

2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA2126-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMMTA92QTA

2N2369ADCSM 2SC2412KT146S 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E

US6T6TR 732314D CMXT3906 TR CPH3121-TL-E CPH6021-TL-H 873787E UMX21NTR EMT2T2R MCH6102-TL-E FP204-TL-E

NJL0302DG 2N3583 2SA1434-TB-E 2SC3143-4-TB-E 2SD1621S-TD-E NTE103 30A02MH-TL-E NSV40301MZ4T1G NTE101 NTE13

NTE15 NTE16001